

AMENDED CLAIMS WITHOUT SHOWING CHANGES MADE

45. The method of claim 33, wherein the layer is further characterized as a barrier layer.
46. The method of claim 45, wherein the barrier layer is further characterized as a tantalum-containing barrier layer
47. The method of claim 33, wherein the aluminum is arc sprayed onto the isolation ring.
48. A method for forming a layer on a wafer, the method comprising the steps of:
placing the wafer within a sputtering chamber, wherein the chamber includes an isolation ring that is coated with a conductive material; and
depositing material from a sputtering target onto the wafer.
49. The method of claim 48, wherein the conductive material is aluminum.
50. The method of claim 49, wherein the aluminum is flame sprayed onto the isolation ring.
51. The method of claim 49, wherein the aluminum is arc sprayed onto the isolation ring.
52. The method of claim 48, wherein the isolation ring includes a ceramic material.
53. The method of claim 48, wherein the isolation ring includes a dielectric material.